# MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PIFD

S9015-MS

Product specification





TRANSISTOR (PNP)

#### **FEATURES**

Complementary to S9014-MS

#### **Reference News**

PACKAGE OUTLINE		MARKING		
1 2	1. BASE 2. EMITTER 3.COLLECTOR	M6		
SOT-23				

## MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>СВО</sub>	Collector-Base Voltage	-50	V
VCEO	Collector-Emitter Voltage	-45	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
lc	Collector Current -Continuous	-0.1	Α
Pc	Collector Power Dissipation	0.2	W
Tj	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55-150	°C

## **ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)**

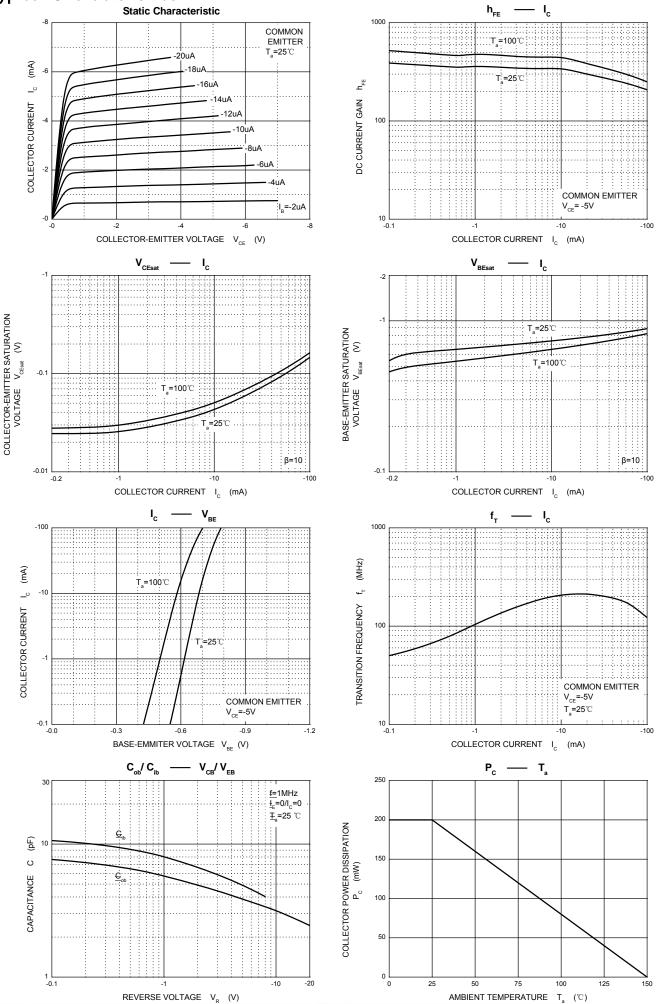
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	l <sub>C</sub> = -100μA, I <sub>E</sub> =0	-50			V
Collector-emitter breakdown voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> = -0.1mA, I <sub>B</sub> =0	-45			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	l <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	Ісво	V <sub>CB</sub> =-50 V, I <sub>E</sub> =0			-0.1	μΑ
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -5V, I <sub>C</sub> =0			-0.1	μΑ
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =-5V, I <sub>C</sub> = -1mA	200		1000	
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> =-100mA, I <sub>B</sub> = -10mA			-0.3	V
Base-emitter saturation voltage	V <sub>BE</sub> (sat)	lc=-100mA, I <sub>B</sub> =-10mA			-1	V
Transition frequency	fτ	V <sub>CE</sub> =-5V, I <sub>C</sub> = -10mA f=30MHz	150			MHz

## **CLASSIFICATION OF hfE(1)**

Rank	L	Н	
Range	200-450	450-1000	

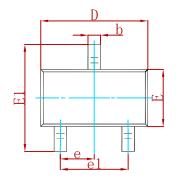


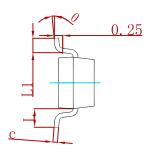
## Typical Characterisitics

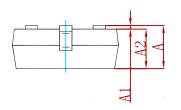




### PACKAGE MECHANICAL DATA

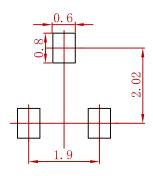






Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.03	7 TYP	
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022	2 REF	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

## **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
- 3. The pad layout is for reference purposes only.

## **REEL SPECIFICATION**

P/N	PKG	QTY
S9015-MS	SOT-23	3000



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